- 1. (Amended) A sputtering target made by a process including casting having a target surface with the following characteristics:
 - a) substantially homogenous composition at any location;
 - b) substantial absence of pores, voids, inclusions and other casting defects;
 - c) an absence of detectable precipitates;
 - d) an average grain size of less than 1µm; and
 - e) substantially uniform structure and texture at any location.
- 2. A sputtering target according to claim 1 comprising one or more of Al, Ti, Cu, Ta, Ni, Mo, Au, Ag, and Pt.
- 3. A sputtering target according to claim 1 comprising AI and about 0.5 wt.% Cu.
- 45. The sputtering target of claim 1 comprising an alloy which includes at least one of Al, Ti, Cu, Ta, Ni, Mo, Au, Ag and Pt.
 - 46. The sputtering target of claim 1 comprising Al.
 - 47. The sputtering target of claim 1 comprising Ti.
 - 48. The sputtering target of claim 1 comprising Cu.

- 49. The sputtering target of claim 1 comprising Ta.
- 50. The sputtering target of claim 1 comprising Ni.
- 51. The sputtering target of claim 1 corporising Mo.
- 52. The sputtering target of claim 1 comprising Au.
- 53. The sputtering target of claim/1 comprising Ag.
- 54. The sputtering target of claim 1 comprising Pt.
- 55. (Amended) A sputtering/target formed from a cast material and comprising:
 a yield strength of greater than 50 mega pascal (MP), and an ultimate tensile
 strength of greater than 125 MP;
 a substantial absence of pores, voids and inclusions; and
 an average grain size of less than about 1 μm.
- 56. The sputtering target of claim 55 comprising one or more of Al, Ti, Cu, Ta, Ni, Mo, Au, Ag, and Pt.
- 57. The sputtering target of claim 55 comprising an alloy which includes at least one of Al, Ti, Cu, Ta, Ni, Mo Au, Ag and Pt.

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The sputtering target of claim 55 further comprising a substantial absence of 58. precipitates. 59. The sputtering target of claim 55 further comprising a substantially uniform structure and texture at any location. The sputtering target of claim 55 further comprising a substantially 60. homogeneous composition at any location. (Amended) A sputtering target comprising copper, formed by a process: 61. including casting, and having a target surface with the following characteristics: substantially homogenous composition at any location; a) substantial absence of pores, voids, inclusions and other casting defects; an absence of detectable precipitates; d) an average grain size less than about 1µm; and substantially uniform structure and texture at any location. e) 62. The sputtering target of claim 1 further comprising one or more of Al, Au, and Ag. 63. The sputtering target of claim 62 comprising Al. 64. The sputtering target of claim 62 comprising Au.

- 65. The sputtering target of claim 62 comprising Ag.
- 66. (Amended) A sputtering target formed from a cast copper material and comprising:

a yield strength of greater than 50 mega Pascal (MP), and an ultimate tensile strength of greater than 125 MP;

a substantial absence of pores, voids and inclusions; and an average grain size of less than about 1 µm.

- 67. The sputtering target of claim 66 wherein the copper material comprises pure copper.
 - 68. 5 The sputtering target of claim 66 comprising one or more of Al, Au, and Ag.
- 69. The sputtering target of claim 66 wherein the copper material comprises a copper alloy having one or more of the elements selected from the group consisting of Al, Au, and Ag.
- 70. The sputtering target of claim 66 further comprising a substantial absence of precipitates.
- 71. The sputtering target of claim 66 further comprising a substantially uniform structure and texture at any location.

- 72. The sputtering target of claim 66 further comprising a substantially homogeneous composition at any location.
- 73. (New) The sputtering target of claim 55 wherein both the yield strength and the ultimate tensile strength are greater than 125 MP.
- 74. (New) The sputtering target of claim 55 wherein both the yield strength and the ultimate tensile strength are greater than 150 MP.